K. J. SOMAIYA COLLEGE OF ENGINEERING DEPARTMENT OF ELECTRONICS ENGINEERING ELECTRONIC CIRCUITS

Design of Single Stage Amplifier

Design 1:

Design a single stage RC coupled JFET amplifier for the following specifications:- $V_{out} = 2V$, $f_L \leq 20Hz$ and $|A_V| \geq 10$ using mid-point biasing technique. Also calculate A_V , Z_i and Z_o of the amplifier you have designed.

Solution:

Step 1:- Data

$$|A_V|=10,\, V_{out}=2V,\, f_L=20Hz$$

Step 2:- Selection of JFET

We select n-channel JFET BFW11 from the datasheet with the following specifications: $g_{m_0} = 5600 \frac{\mu A}{V}$, $V_P = -2.5V$, $r_d = 50k\Omega$ and $I_{DSS} = 7mA$

Step 3:- Selection of biasing circuit

Self-bias circuit is used to give mid-point biasing

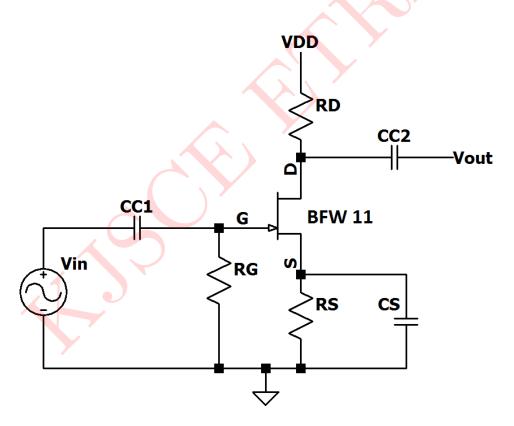


Figure 1: Circuit 1

Step 4:- Selection of Q-point

(i) For midpoint biasing,
$$I_D = \frac{I_{DSS}}{2}$$

i.e.
$$I_D = \frac{7mA}{2} = 3.5mA$$

(ii)
$$I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P}\right)^2$$

$$\frac{3.5}{7} = \left(1 - \frac{V_{GS}}{V_P}\right)^2$$

$$0.5 = \left(1 + \frac{V_{GS}}{2.5}\right)^2$$

$$\sqrt{0.5} = 1 + \frac{V_{GS}}{2.5}$$

$$V_{GS} = (\sqrt{0.5} - 1) \times 2.5$$

$V_{GS} = -0.732$

(iii)
$$g_m = g_{m_o} \left(1 - \frac{V_{GS}}{V_P} \right)$$

$$g_m = 5600 \times 10^{-6} \left(1 - \frac{0.732}{2.5} \right) = 3.96 mA/V$$

$$g_m=3.96mA/V$$

Step 5:- Selection of R_S

$$V_{GS} = I_D R_S$$
 [Self Bias]

$$R_S = \frac{-V_{GS}}{I_D} = \frac{0.732}{3.5mA} = 209\Omega$$

Select
$$R_S = 220\Omega$$
, $1/4W$

Step 6:- Selection of R_D

$$A_V = -g_m(r_d||R_D)$$

$$-10 = -3.9 \frac{mA}{V} \left(\frac{50k\Omega \times R_D}{R_D + 50k\Omega} \right)$$

$$\frac{10k}{3.96} = \frac{50k\Omega \times R_D}{50k\Omega + R_D}$$

$$50k + R_D = 19.8R_D$$

$$R_D = 2.67k\Omega$$

Select
$$R_D = 2.7k\Omega$$
, $1/4W$

Step 7:- Selection of R_G

Select
$$R_G = 1M\Omega$$
, $1/4W$

Step 8:- Selection V_{DD}

$$\begin{split} V_{DS} &\geq V_{o_{peak}} + |V_P| & [V_{o_{RMS}} = 2V \text{ and } V_{o_{peak}} = 2\sqrt{2}] \\ V_{DS} &= 1.5(V_{o_{peak}} + 2.5) \\ V_{DS} &= 1.5(2\sqrt{2} + 2.5) \\ V_{DS} &\approx 8V \end{split}$$

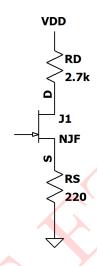


Figure 2: D to S Loop

Applying KVL to the Drain-Source loop:-

$$V_{DD} - I_D R_D - V_{DS} - I_D R_S = 0$$

 $V_{DD} = V_{DS} + I_D (R_D + R_S)$
 $V_{DD} = 8 + 3.5 mA (2.7k\Omega + 220\Omega) = 18.22V$
Select $V_{DD} = 20V$

Step 9:- Selection of C_S

$$X_{C_S} \le 0.1 R_S$$

$$\frac{1}{2\pi f_{L_{CS}} \le 0.1 R_S} \qquad [f_{L_{CS}} = f_L = 20 Hz]$$

$$C_S \ge \frac{1}{2\pi f_L \times 0.1 R_S} \ge \frac{1}{2\pi 20 \times 0.1 \times 220}$$

$$C_S \ge 361.715 \mu F$$
 Select $C_S = 390 \mu F/25 V$

Step 10:- Selection of C_{C_1}

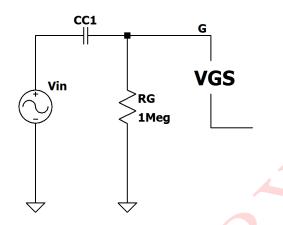


Figure 3: Small Signal low frequency equivalent circuit for C_{C_1}

$$C_{C_1} = \frac{1}{2\pi f_{L_{CC_1}} R_{eq}}$$
 $R_{eq} = 1M\Omega = R_G$
i.e. $C_{C_1} = \frac{1}{2\pi 20 \times 1M\Omega} = 7.95nF$
Select, $C_{C_1} = 8.2nF/25V$

Step 11:- Selection of C_{C_2}

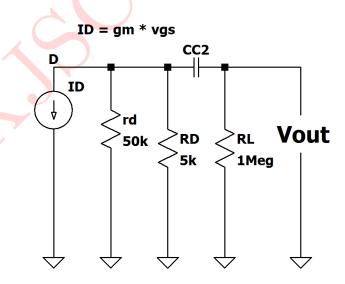


Figure 4: Small Signal low frequency equivalent circuit for C_{C_2}

$$\begin{split} C_{C_2} &= \frac{1}{2\pi f_{L_{CC_2}} R_{eq}} \\ R_{eq} &= (r_d || R_D) + R_L \\ R_L &= R_G = 1M\Omega \qquad [\because R_L \text{ is not given, } R_L = R_{i_{nextstage}}] \\ R_{eq} &= (2.7k\Omega || 50k\Omega) + 1M\Omega \approx 1M\Omega \\ C_{C_2} &= \frac{1}{2\pi \times 1 \times 10^6 \times 20} = 7.95 \mu F \\ \text{Select, } C_{C_2} &= 8.2nF/25V \end{split}$$

Step 12:- Designed Circuit

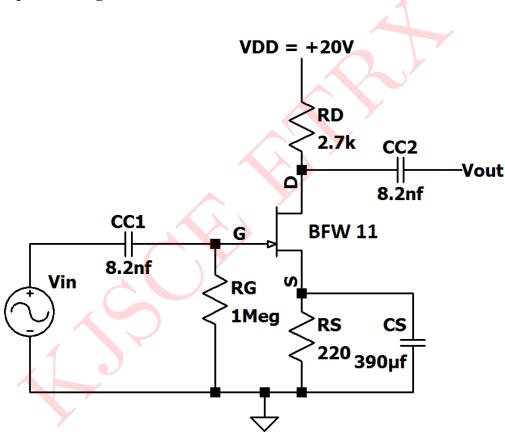


Figure 5: Designed Circuit

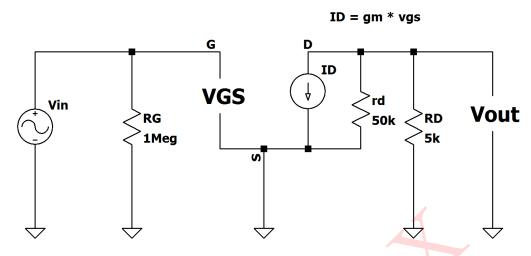


Figure 6: Small Signal Equivalent Circuit

$$A_V = -g_m(R_D||r_d)$$

$$A_V = -3.96 \frac{mA}{V} \left(\frac{2.7k\Omega \times 50k\Omega}{52.7k\Omega}\right) = -10.15$$

$$A_V = -10.15$$

Input Impedance:-

$$Z_i = R_G = 1M\Omega$$

$$Z_i=1M\Omega$$

Output Impedance:-

$$Z_o = R_D || r_d = \left(\frac{2.7k\Omega \times 50k\Omega}{52.7k\Omega} \right) = 2.56k\Omega$$

 $Z_o = 2.56k\Omega$

SIMULATED RESULTS:

Above circuit was simulated in LTSpice and results are presented below:

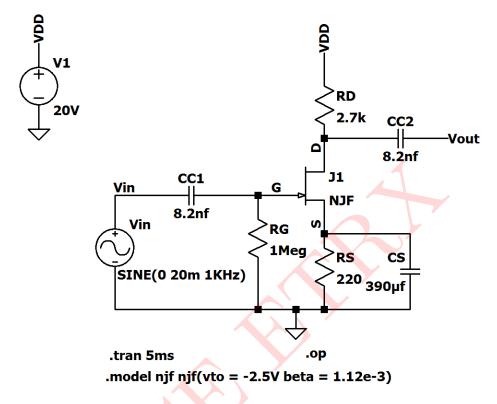


Figure 7: Circuit Schematic 1

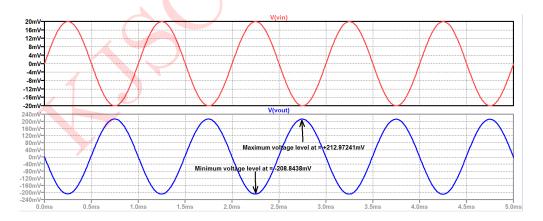


Figure 8: Input & Output waveform

Comparison of Theoretical and Simulated Values:

Parameters	Theoretical	Simulated
I_D	3.5mA	3.42mA
A_V	-10.15	-10.51

Table 1: Design 1

